

N-Ch 20V Fast Switching MOSFETs

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary



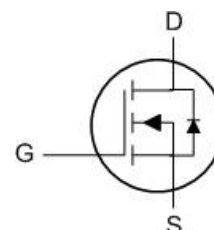
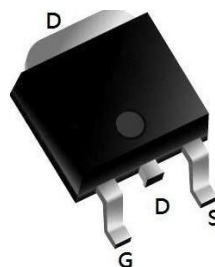
BVDSS	RDSON	ID
20V	4.8 mΩ	60A

Description

The XR60N02 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The XR60N02 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO252-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ¹	60	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V ¹	35	A
I_{DM}	Pulsed Drain Current ²	240	A
EAS	Single Pulse Avalanche Energy ³	48	mJ
I_{AS}	Avalanche Current	31	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	38	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	4.2	$^\circ\text{C/W}$

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Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.4	0.7	1.0	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =4.5V, I _D =25A	-	4.8	6.5	mΩ
		V _{GS} =2.5V, I _D =15A	-	6.8	10	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1.0MHz	-	1832	-	pF
C _{oss}	Output Capacitance		-	289	-	pF
C _{rss}	Reverse Transfer Capacitance		-	271	-	pF
Q _g	Total Gate Charge	V _{DS} =10V, I _D =25A, V _{GS} =4.5V	-	23	-	nC
Q _{gs}	Gate-Source Charge		-	4.5	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	7.3	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =10V, I _D =25A, R _{GEN} =3Ω, V _{GS} =4.5V	-	15	-	ns
t _r	Turn-on Rise Time		-	37	-	ns
t _{d(off)}	Turn-off Delay Time		-	52	-	ns
t _f	Turn-off Fall Time		-	21	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	60	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	240	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =30A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	IF=25A, dI/dt=100A/μs	-	25	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	21	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=10V$, $V_G=4.5V$, $L=0.5mH$, $R_G=25\Omega$, $I_{AS}=13.8A$ 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

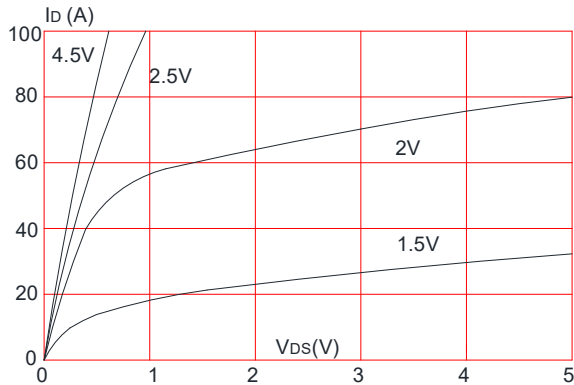


Figure 2: Typical Transfer Characteristics

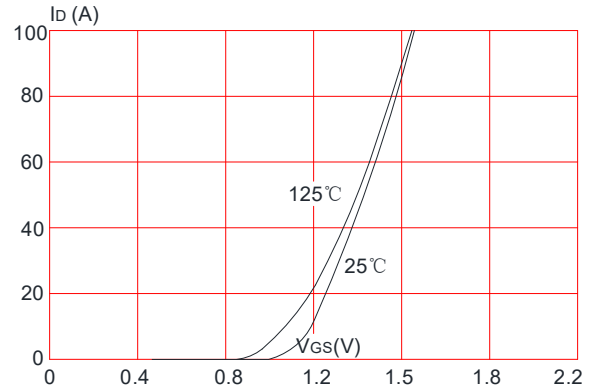


Figure 3: On-resistance vs. Drain Current

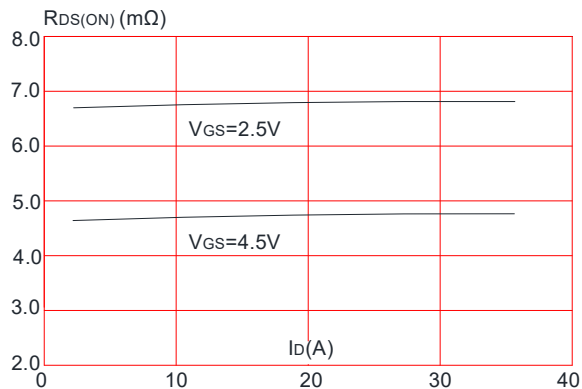


Figure 4: Body Diode Characteristics

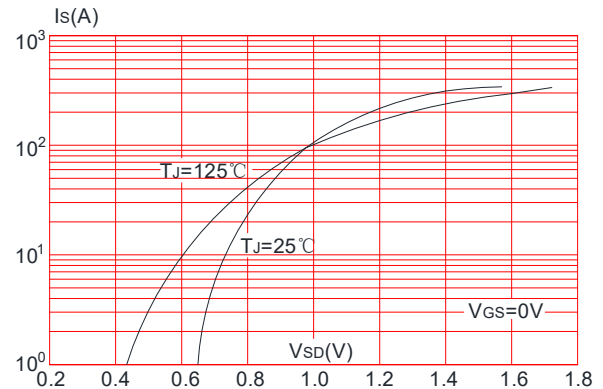


Figure 5: Gate Charge Characteristics

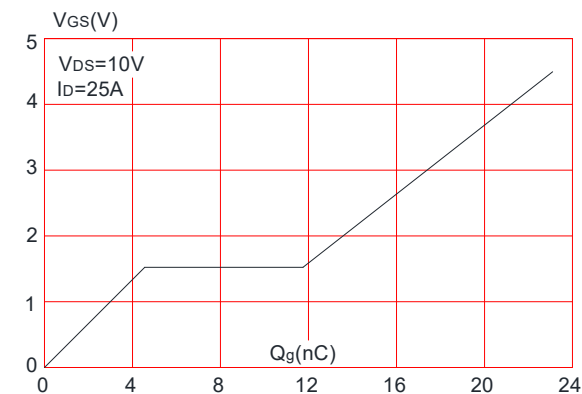
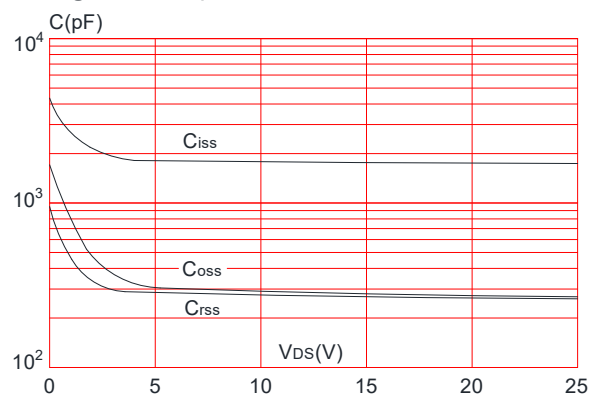


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

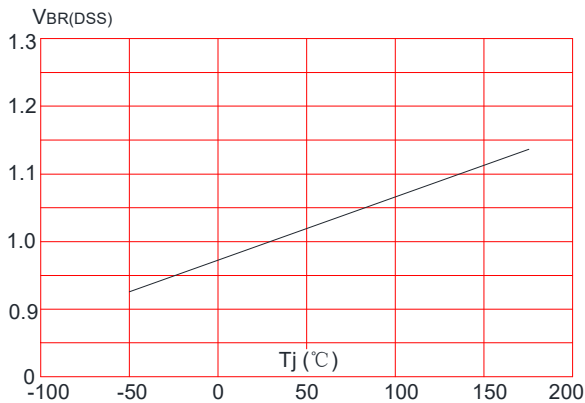


Figure 8: Normalized on Resistance vs. Junction Temperature

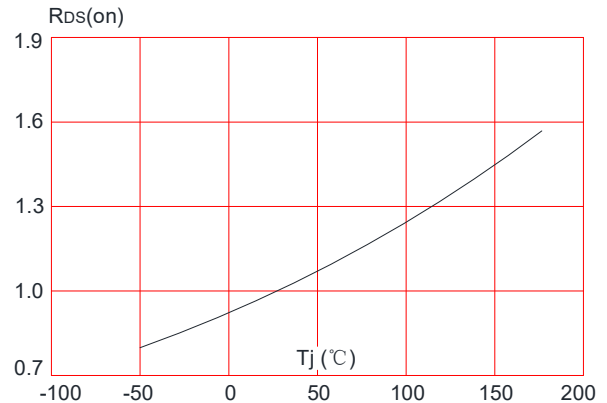


Figure 9: Maximum Safe Operating Area

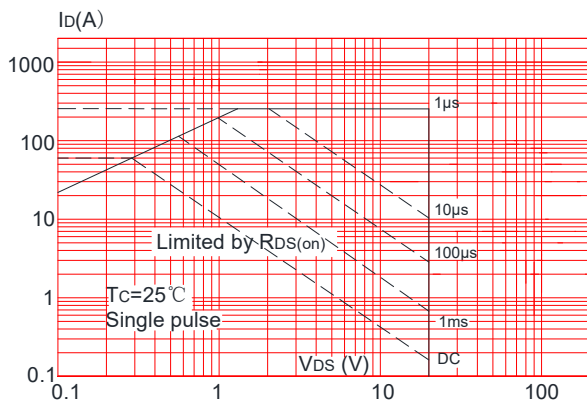


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

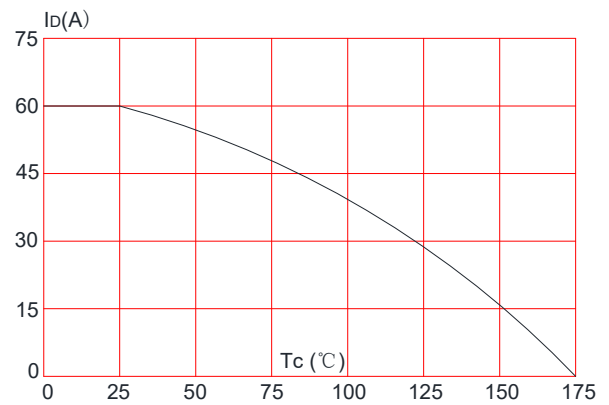
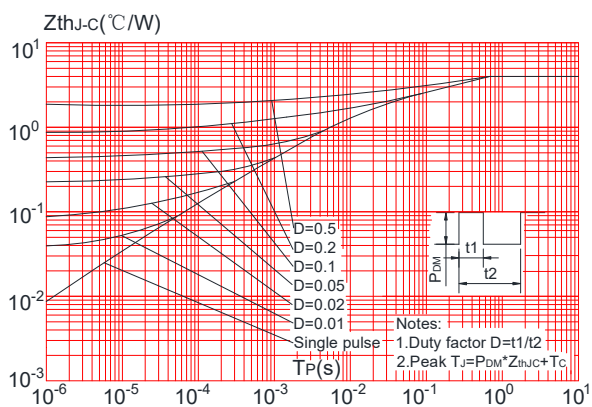
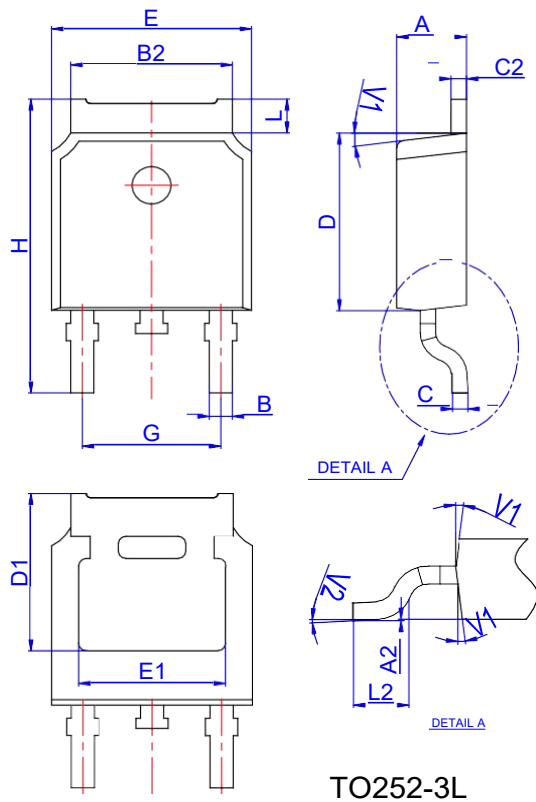


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



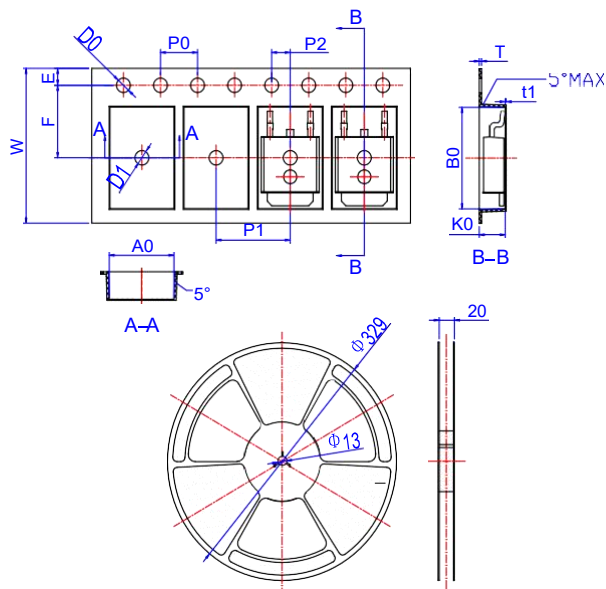
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Package Mechanical Data TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583